

Bipolar PNP Bare Die – BTP6975

Part Description

The BTP6975 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -80V
- VCEO = -60V
- VEBO = -6V
- hFE = 200-400 @ VCE = -2V, IC = -0.1A
- · VCE(Sat) = -0.3V @ IC = -1A, IB = -33mA
- · fT = 180 MHz @ VCE = -2V, IE = 0A
- COBO = 20pF @ VCB = -10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to ON SEMI KSB1116A

Die Size (Unsawn)

790µm X 790µm, 31 Mils X 31 Mils

This is a shortform datasheet only For the full datasheet

Please contact sales@siliconsupplies.com

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